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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/733,289	12/08/2000	Xiao-Chun Mu	42390P8875	2980
21186	7590	05/02/2006	EXAMINER	
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A. P.O. BOX 2938 MINNEAPOLIS, MN 55402			NGUYEN, DILINH P	
			ART UNIT	PAPER NUMBER
			2814	

DATE MAILED: 05/02/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

## Office Action Summary

Application No.

09/733,289

Applicant(s)

MU ET AL.

Examiner

DiLinh Nguyen

Art Unit

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☒ Responsive to communication(s) filed on 07 April 2006.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-4, 10-17 and 29 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-4, 10-17, 29 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

### Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
  - ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

### Attachment(s)

- ☐ Notice of References Cited (PTO-892)
- ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date \_\_\_\_\_
- ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date. \_\_\_\_\_
- ☐ Notice of Informal Patent Application (PTO-152)
- ☐ Other: \_\_\_\_\_

## DETAILED ACTION

### *Claim Rejections - 35 USC § 103*

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claim 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over Chen et al. (U.S. Pat. 6160311) (previously applied) in view of Jimarez et al. (U.S. Pat. 6407334) (previously applied).

Chen et al. disclose a semiconductor device (cover fig.) comprising:

a heat sink 32 (column 3, lines 30-31);

at least one microelectronic die 31 having an active surface and a back surface,

wherein at least one microelectronic die back surface adjacent to the heat sink;

a patterned adhesive layer 33 disposed between the die 31 and the heat sink 32;

and

an encapsulation material 36 (column 3, lines 58-59) disposed on the heat sink

and the microelectronic die active surface.

Chen et al. fail to disclose the patterned adhesive layer 33 is a patterned thermally conductive adhesive.

Jimarez et al. disclose a patterned thermally conductive adhesive layer 44 (cover fig., column 3, lines 27-28) disposed between the at least one chip 34 and a heat sink

46. Therefore, it would have been obvious to one having ordinary skill in the art at the

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time the invention was made to modify the device of Chen et al. to increase the heat dissipation between the die and the heat sink, as shown by Jimarez et al.

3. Claim 29 is rejected under 35 U.S.C. 103(a) as being unpatentable over Chen et al. (U.S. Pat. 6160311) (previously applied) in view of Jimarez et al. (U.S. Pat. 6407334) (previously applied) as applied to claim 1 above, and further in view of Woodward et al. (U.S. Pat. 4731700) (previously applied).

Chen et al. fail to disclose a microelectronic package core and wherein at least one die is disposed within at least one package core opening.

Woodward et al. disclose a semiconductor device (fig. 2, column 4, lines 12-24) comprising:

a ceramic member 14 having a first surface and an opposing second surface, the ceramic member having at least one opening defined therein extending from the ceramic member first surface to the ceramic member second surface, where the ceramic member second surface abuts the heat sink 12; and

wherein at least one die 16 is disposed within the ceramic member opening and adjacent the heat sink, the die having an active surface. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Chen et al. to provide an electrical crossover in the area above the die and increase in interconnect density, as shown by Woodward et al.

4. Claims 1-4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Eichelberger (U.S. Pat. 5250843) (previously applied) in view of Jimarez et al. (U.S. Pat. 6407334) (previously applied).

Eichelberger discloses a semiconductor device (fig. 1, column 13, lines 51 et seq.) comprising:

- a heat sink 12 ;
- at least one microelectronic die 14 having an active surface and a back surface, wherein at least one microelectronic die back surface adjacent to the heat sink;
- a thin die attach material 16 disposed between the die and the heat sink (column 13, lines 64-66); and
- an encapsulation material 18 disposed on the heat sink and the die active surface.

Eichelberger fails to disclose a thin die attach material 16 is a patterned thermally conductive adhesive layer.

Jimarez et al. disclose a patterned thermally conductive adhesive layer 44 (cover fig., column 3, lines 27-28) disposed between the at least one chip 34 and a heat sink 46. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Eichelberger to increase the heat dissipating between the die and the heat sink, as shown by Jimarez et al.

- Regarding claim 2, Eichelberger discloses a build up layer disposed on an upper surface of the encapsulant material.
- Regarding claim 3, Eichelberger discloses the build up layer comprises at least on conductive trace 20 disposed on the encapsulation material upper surface, wherein a portion of the conductive trace extending through the encapsulation material to contact the microelectronic die active surface.

- Regarding claim 4, Eichelberger discloses the build up layer further includes at least one dielectric layer 24 disposed on at least a portion of the encapsulation material upper surface and at least on conductive trace, and at least one second conductive trace 26 extending through the dielectric layer to contact the conductive trace.

5. Claim 29 is rejected under 35 U.S.C. 103(a) as being unpatentable over Eichelberger (U.S. Pat. 5250843) (previously applied) in view of Jimarez et al. (U.S. Pat. 6407334) (previously applied) as applied to claim 1 above, and further in view of Woodward et al. (U.S. Pat. 4731700) (previously applied).

Eichelberger fails to disclose a microelectronic package core and wherein at least one die is disposed within at least one package core opening.

Woodward et al. disclose a semiconductor device (fig. 2, column 4, lines 12-24) comprising:

a ceramic member 14 having a first surface and an opposing second surface, the ceramic member having at least one opening defined therein extending from the ceramic member first surface to the ceramic member second surface, where the ceramic member second surface abuts the heat sink 12; and

wherein at least one die 16 is disposed within the ceramic member opening and adjacent the heat sink, the die having an active surface. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Eichelberger to provide an electrical crossover in the area above the die and increase in interconnect density, as shown by Woodward et al.

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6. Claims 10 and 15-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shen (U.S. Pat. 6368894) (previously applied) in view of Woodward et al. (U.S. Pat. 4731700) (previously applied).

Shen discloses a semiconductor device (figs. 1-2, column 4, lines 5 et seq.) comprising:

a heat sink 33 (column 5, lines 27);

a package core 1 having a first surface 10 and an opposing second surface 14, the package core having at least one opening 11 (fig. 2) defined therein extending from the package core first surface to the package core second surface;

at least one die 3 (column 5, lines 30) disposed within at least one package core opening and adjacent the heat sink, at least one die having an active surface; and

an encapsulation material 34 disposed on the die and in portions of at least one package core opening.

Shen fails to disclose where the microelectronic package core second surface abuts the heat sink.

Woodward et al. disclose a semiconductor device (fig. 2, column 4, lines 12-24) comprising: a ceramic member 14 having a first surface and an opposing second surface, wherein the ceramic member second surface abuts a heat sink 12. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Shen to provide good heat dissipation for the semiconductor package device, as shown by Woodward et al.

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- Regarding claim 15, Woodward et al. disclose a thickness of the ceramic member 14 is greater than a thickness of at least one die 16.
- Regarding claim 16, Shen discloses the package core is a material selected from the group consisting of ceramics or metals (column 4, lines 5-10).

7. Claims 11-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shen (U.S. Pat. 6368894) (previously applied) in view of Woodward et al. (U.S. Pat. 4731700) (previously applied) as applied to claim 10 above, and further in view of Eichelberger (U.S. Pat. 5250843) (previously applied).

Shen fails to disclose a build up layer disposed on an upper surface of the encapsulation material.

Eichelberger discloses a semiconductor device (fig. 1, column 13, lines 51 et seq.) comprising: a build up layer disposed on an upper surface of the encapsulation material 18 to provide interconnection pads (column 10, lines 54-57). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Shen to provide a direct interconnection between integrated circuit chips, as shown by Eichelberger.

- Regarding claim 12, Eichelberger discloses the build up layer comprises at least on conductive trace 20 disposed on the encapsulation material upper surface, wherein a portion of the conductive trace extending through the encapsulation material to contact the microelectronic die active surface.
- Regarding claim 13, Eichelberger discloses the build up layer further includes at least one dielectric layer 24 disposed on at least a portion of the encapsulation



material upper surface and at least on conductive trace, and at least one second conductive trace 26 extending through the dielectric layer to contact the conductive trace.

- Regarding claim 14, Shen discloses the encapsulation (34 and 24) covers the package core first surface.

8. Claim 17 is rejected under 35 U.S.C. 103(a) as being unpatentable over Shen (U.S. Pat. 6368894) (previously applied) in view of Woodward et al. (U.S. Pat. 4731700) (previously applied) as applied to claim 10 above, and further in view of Jimarez et al. (U.S. Pat. 6407334) (previously applied).

Shen fails to disclose a patterned thermally conductive adhesive layer.

Jimarez et al. disclose a patterned thermally conductive adhesive layer 44 (cover fig., column 3, lines 27-28) disposed between the at least one chip 34 and a heat sink 46. Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Shen to increase the heat dissipation between the die and the heat sink, as shown by Jimarez et al.

### ***Response to Arguments***

Applicant's arguments filed 4/7/06 have been fully considered but they are not persuasive.

The applicant argues that a single structure layer 44 of Jimarez is outside the meaning of "patterned" as disclosed and claimed by Applicant. In fig. 2 where two occurrences of the adhesive layer 140 is "patterned" within the meaning of the claims.

There is no layer 140 in Applicant's fig. 2.

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The arguments have been fully considered but they are not persuasive because Jimarez et al. disclose a thermally conductive adhesive layer 44 (cover fig., column 3, lines 27-28) disposed between the at least one chip 34 and a heat sink 46. The thermally conductive adhesive layer 44 is clearly patterned between the chip 34 and the heat sink 46. Therefore, layer 44 of Jimarez et al. (cover fig.) is a patterned thermally conductive adhesive.

### ***Conclusion***

Any inquiry concerning this communication or earlier communications from the examiner should be directed to DiLinh Nguyen whose telephone number is (571) 272-1712. The examiner can normally be reached on 8:00AM - 6:00PM (M-F).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on (571) 272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

DLN



HOAI PHAM  
PRIMARY EXAMINER